

Description

The SI2309A uses advanced trench technology and design to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge .This device is well suited for use as a load switch or in PWM applications.



General Features

 V_{DS} =-60V,I $_{D}$ =-1.6A

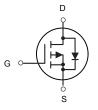
 $R_{DS(ON)}$ <160m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <200m Ω @ V_{GS} =-4.5V

Application

Load switch

PWM application



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SI2309A	SOT-23	2309	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-60	V
Vgs	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-1.6	А
Ірм	Drain Current-Pulsed (Note 1)	-8	А
P _D	Maximum Power Dissipation	1.5	W
Тл,Твтв	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	83.3	°C/W



Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			1	JI.		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -60		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V		-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)			•	•		•
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA -1.4		-2.0	-2.6	V
Drain Course On State Desistance	В	V _{GS} =-10V, I _D =-1.5A	-	140	160	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-1.5A	-	160	200	mΩ
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-1.5A	-	3	-	S
Dynamic Characteristics (Note4)			•	•		•
Input Capacitance	C _{lss}	.,	-	444.2	-	PF
Output Capacitance	C _{oss}	V_{DS} =-30V, V_{GS} =0V,	-	19.6	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	17.9	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	40	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, I_{D} =-1.5A,	-	35	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =3 Ω	-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V 00 L 4.5A	-	11.3	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-30, I_{D} =-1.5A, V_{GS} =-10V	-	2.7	-	nC
Gate-Drain Charge	Q_{gd}	VGS=-10V	-	1.6	-	nC
Drain-Source Diode Characteristics						•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.5A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-1.6	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 1.5A	-	25		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	31		nC
				•		•

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics (Curves)

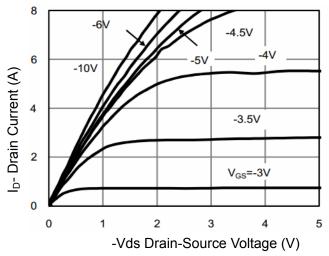


Figure 1 Output Characteristics

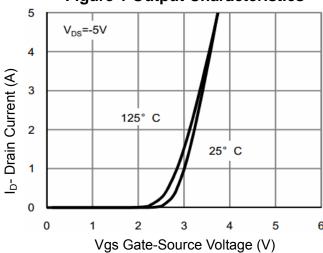
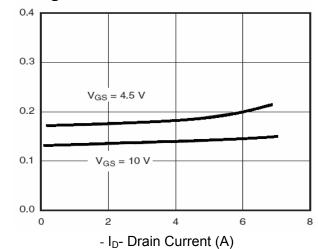


Figure 2 Transfer Characteristics



Rdson On-Resistance(()

Figure 3 Rdson- Drain Current

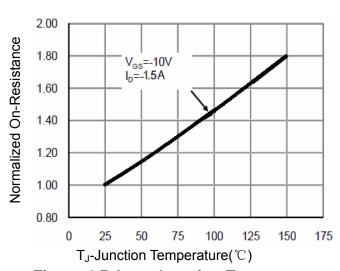
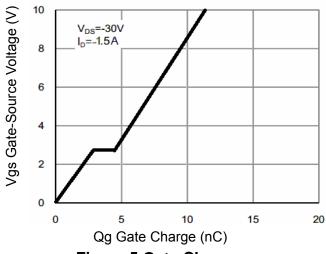


Figure 4 Rdson-Junction Temperature



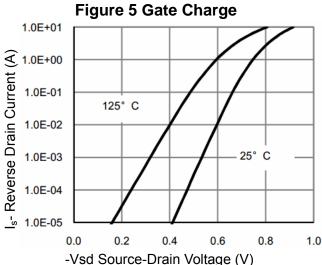


Figure 6 Source- Drain Diode Forward



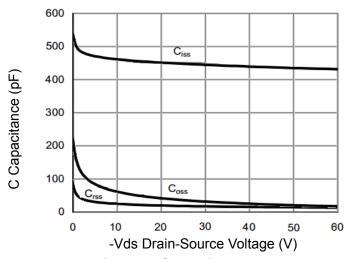


Figure 7 Capacitance vs Vds

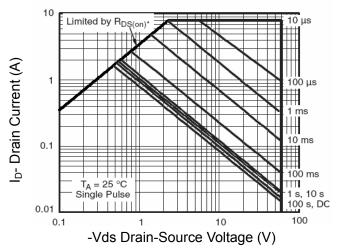


Figure 8 Safe Operation Area

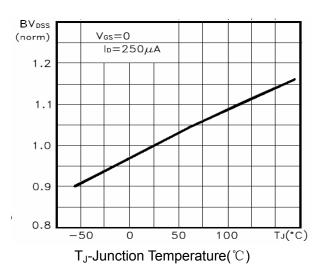


Figure 9 BV_{DSS} vs Junction Temperature

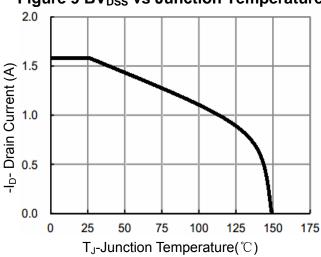
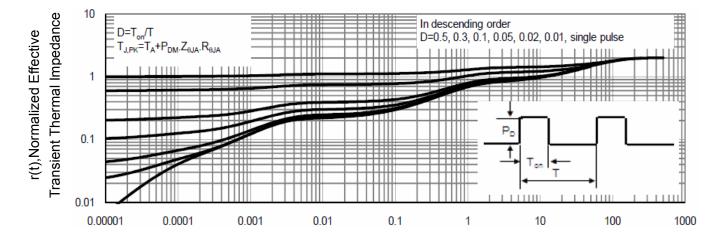


Figure 10 ID Current De-rating



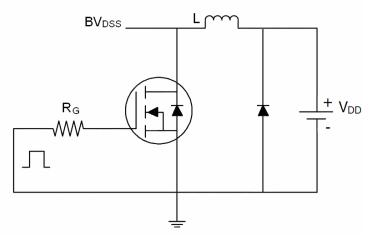
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

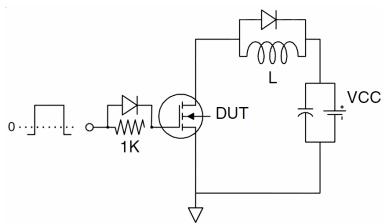


Test Circuit

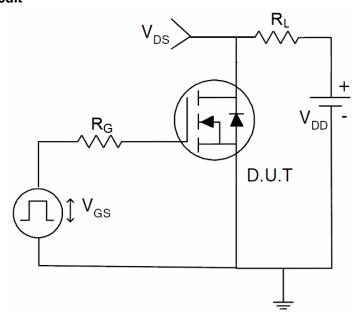
1) E_{AS} test Circuit



2) Gate charge test Circuit

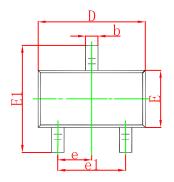


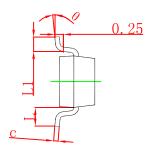
3) Switch Time Test Circuit

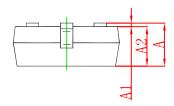




SOT-23 Package Outline Dimensions

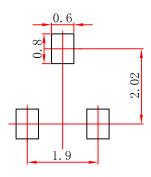






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	0 TYP 0.037 TYP		7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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